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FDC6310P

Dual P-Channel 2.5V Specified PowerTrench® MOSFET

General Description

These P-Channel 2.5V specified MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

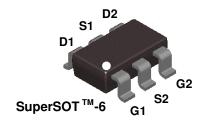
These devices have been designed to offer exceptional power dissipation in a very small footprint for applications where the bigger more expensive SO-8 and TSSOP-8 packages are impractical.

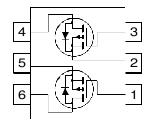
Applications

- · Load switch
- · Battery protection
- Power management

Features

- -2.2 A, -20 V. $R_{DS(ON)}$ = 125 $m\Omega$ @ V_{GS} = -4.5 V $R_{DS(ON)}$ = 190 $m\Omega$ @ V_{GS} = -2.5 V
- · Low gate charge
- Fast switching speed
- High performance trench technology for extremely low R_{DS(CN)}
- SuperSOT TM -6 package: small footprint 72% smaller than standard SO-8); low profile (1mm thick)





Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-20	V
V _{GSS}	Gate-Source Voltage		±12	V
I _D	Drain Current - Continuous	(Note 1a)	-2.2	Α
	- Pulsed		-6	
P _D	Power Dissipation for Single Operation	(Note 1a)	0.96	W
		(Note 1b)	0.9	
		(Note 1c)	0.7	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

R _{0JA}	Thermal Resistance, Junction-to-Ambient	(Note 1a)	130	°C/W
ReJC	Thermal Resistance, Junction-to-Case	(Note 1)	60	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.310 FDC6310P 7"		7"	8mm	3000 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics		1	ı		
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu A$, Referenced to 25°C		-11		mV/°C
l _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
GSSF	Gate-Body Leakage, Forward	$V_{GS} = 12 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -12 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)		•		•	
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.6	-1.0	-1.5	٧
ΔV _{GS(th)} ΔT _J	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$, Referenced to 25°C		3		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = -4.5 \text{ V}, I_D = -2.2 \text{ A}$ $V_{GS} = -2.5 \text{ V}, I_D = -1.8 \text{ A}$ $V_{GS} = -4.5 \text{ V}, I_D = -2.2 \text{ A}, T_J = 125^{\circ}\text{C}$		100 145 137	125 190 184	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$	-6			Α
g FS	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_{D} = -3.5 \text{ A}$		6		S
Dynamic	Characteristics			•	•	
Ciss	Input Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$		337		pF
Coss	Output Capacitance	f = 1.0 MHz		88		pF
C _{rss}	Reverse Transfer Capacitance			51		pF
Switchin	g Characteristics (Note 2)			•	•	
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -10 \text{ V}, \qquad I_D = -1 \text{ A},$		9	18	ns
t _r	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, \qquad R_{GEN} = 6 \Omega$		12	22	ns
t _{d(off)}	Turn-Off Delay Time			10	20	ns
t _f	Turn-Off Fall Time			5	10	ns
Qg	Total Gate Charge	$V_{DS} = -10 \text{ V}, \qquad I_D = -2.2 \text{ A}, \\ V_{GS} = -4.5 \text{ V}$		3.7	5.2	nC
Q _{gs}	Gate-Source Charge			0.65		nC
Q _{gd}	Gate-Drain Charge	1		1.3		nC
Drain-Se	ource Diode Characteristics	and Maximum Ratings	ı		ı	
ls	Maximum Continuous Drain-Source	•			-0.8	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -0.8 \text{ A} \text{(Note 2)}$		0.77	-1.2	V

Notes

1. $R_{\theta,N}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta,N}$ is guaranteed by design while $R_{\theta,N}$ is determined by the user's board design.



a) 130 °C/W when mounted on a 0.125 in² pad of 2 oz. copper.



b) 140°/W when mounted on a .004 irr² pad of 2 oz copper



c) 180°/W when mounted on a minimum pad.

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width < $300\mu s$, Duty Cycle < 2.0%

Typical Characteristics

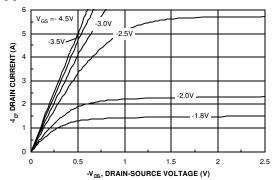
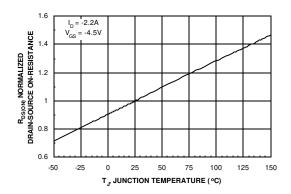


Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.



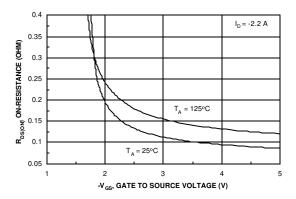
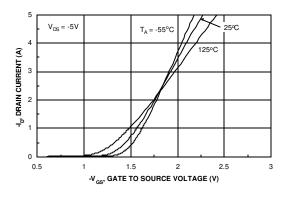


Figure 3. On-Resistance Variation with Temperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



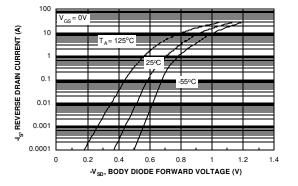
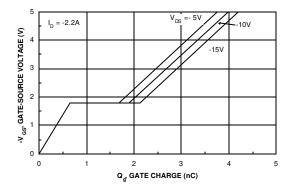


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



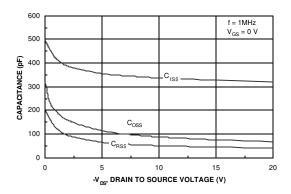
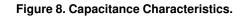
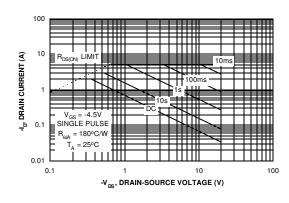


Figure 7. Gate Charge Characteristics.





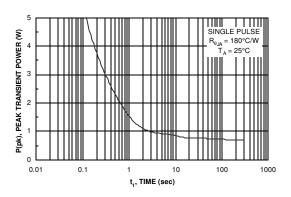


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

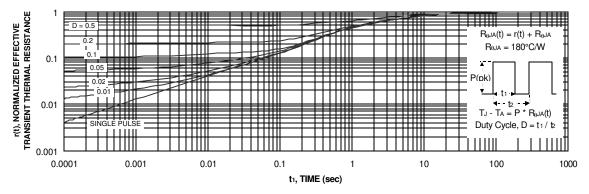


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient themal response will change depending on the circuit board design.

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